

Supporting Information

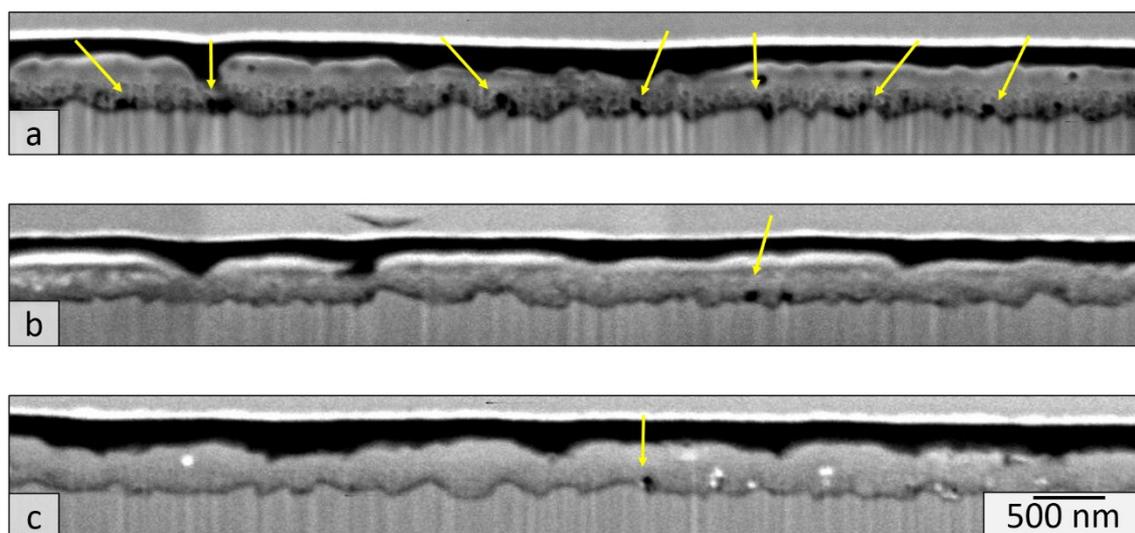


Figure S1 SEM cross sectional views of fresh a), b) and stressed c) devices. The images were acquired from central a) and peripheral regions b), c).

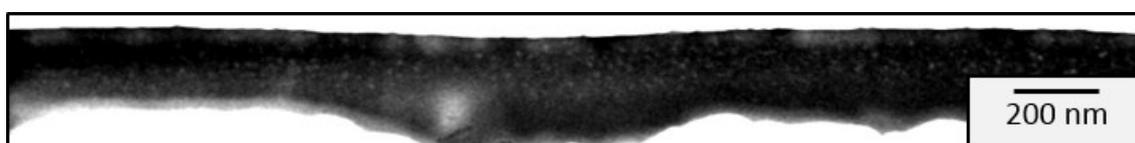


Figure S2. HAADF STEM image with increased contrast of the hole transport layer.

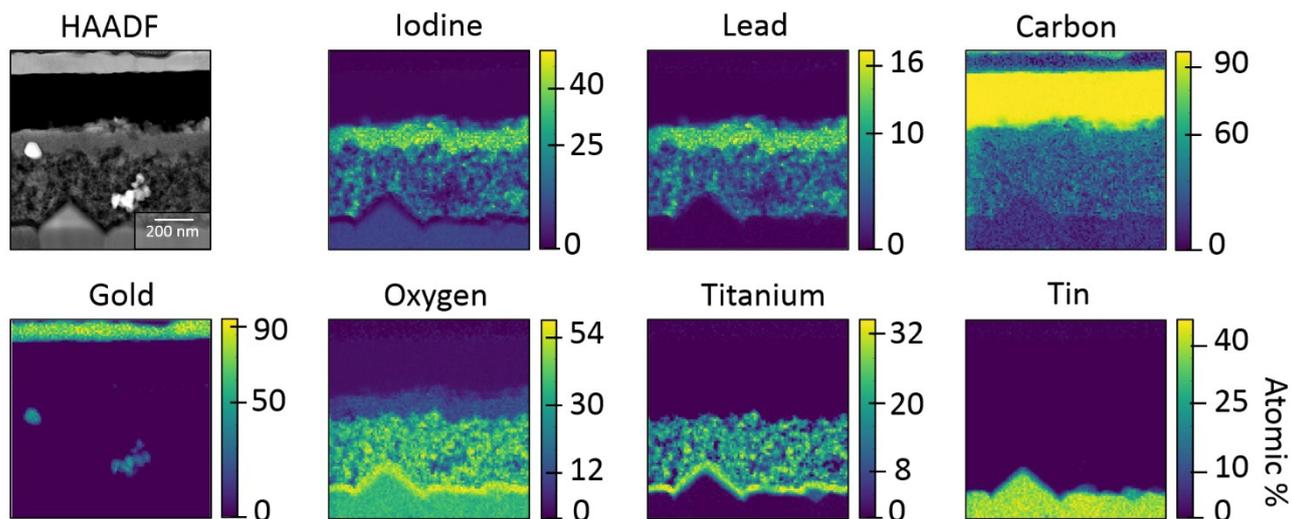


Figure S3. HAADF image and elemental quantitative EDX maps after 220 h light soaking for Iodine, Lead, Carbon, Gold, Oxygen, Titanium and Tin.

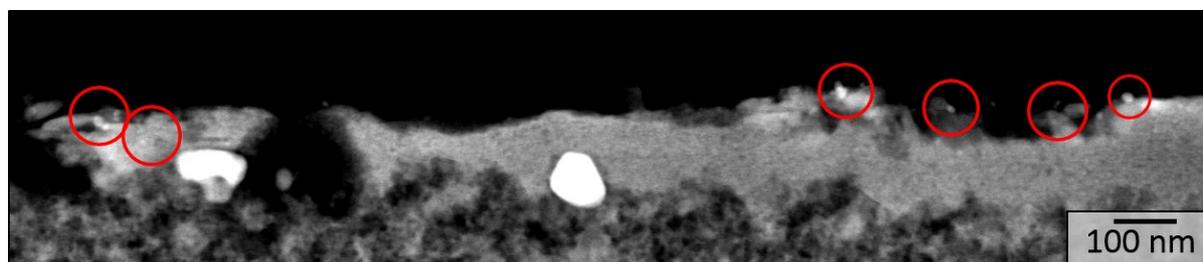


Figure S4. HAADF STEM image of a device after 220h light soaking test showing gold aggregates formation at the interface HTL/Perovskite (red circles).